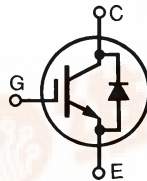




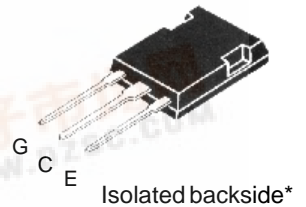
# HiPerFAST™ IGBT with Diode ISOPLUS247™ (Electrically Isolated Backside)

$V_{CES} = 600 \text{ V}$   
 $I_{C25} = 45 \text{ A}$   
 $V_{CE(SAT)typ} = 2.1 \text{ V}$   
 $t_{fi(typ)} = 55 \text{ ns}$



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	45	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	28	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	120	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 64$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	140	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1 \text{ min leads-to housing}$	2500	V~
<b>Weight</b>		5	g

ISOPLUS 247™ (IXGR)  
 E 153432



G = Gate, C = Collector,  
 E = Emitter, TAB = Collector

\* Patent pending

### Features

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

### Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

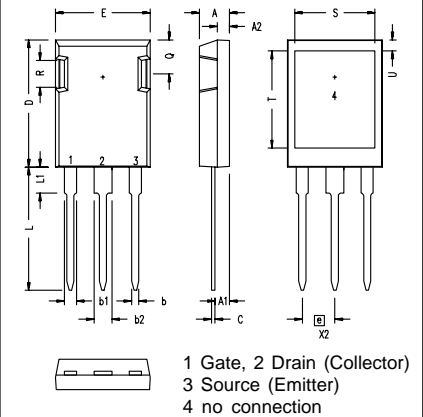
### Advantages

- Easy assembly
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			$T_J = 25^\circ\text{C}$ 200 $\mu\text{A}$ $T_J = 125^\circ\text{C}$ 3 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_T, V_{GE} = 15 \text{ V}$ Note 1	2.1	2.5	V



Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_T; V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$		25	S
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		2700	pF
$C_{oes}$			240	pF
$C_{res}$			50	pF
$Q_g$	$I_C = I_T, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		110	nC
$Q_{ge}$			22	nC
$Q_{gc}$			40	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_T, V_{GE} = 15\text{ V}, L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 4.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		25	ns
$t_{ri}$			20	ns
$t_{d(off)}$			85	ns
$t_{fi}$			55	ns
$E_{off}$			0.32	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_T, V_{GE} = 15\text{ V}, L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 4.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		25	ns
$t_{ri}$			25	ns
$E_{on}$			1	mJ
$t_{d(off)}$			110	170 ns
$t_{fi}$			100	160 ns
$E_{off}$		0.85	1.25 mJ	
$R_{thJC}$				0.90 K/W
$R_{thCK}$		0.15		K/W

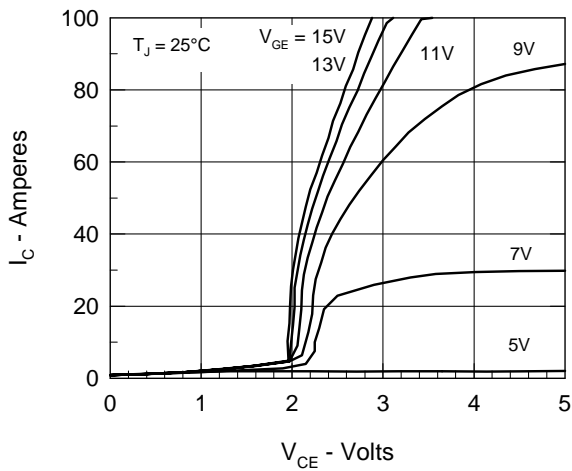
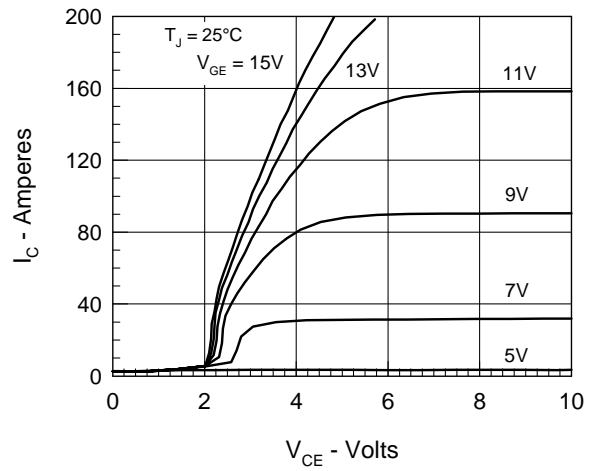
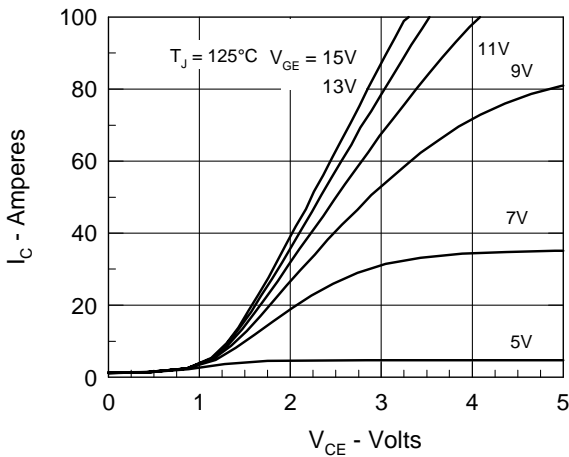
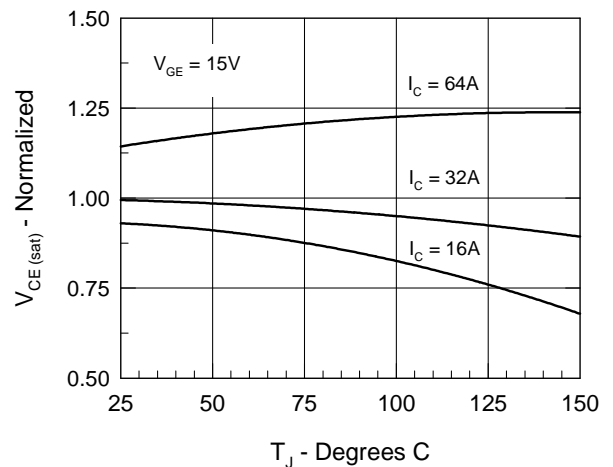
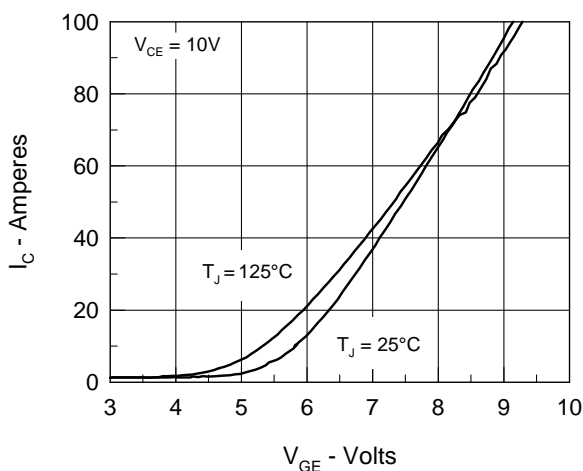
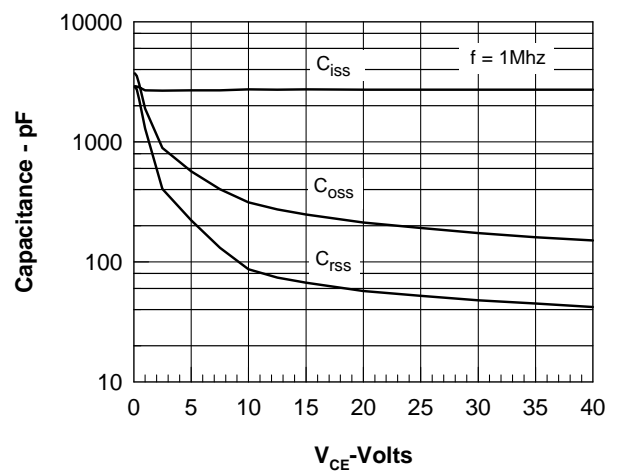
**ISOPLUS 247 (IXGR) OUTLINE**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215	BSC
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080

**Reverse Diode (FRED)**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = I_T, V_{GE} = 0\text{ V}$ , Pulse test $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$	$T_J = 150^\circ\text{C}$		1.6 V
		$T_J = 25^\circ\text{C}$		2.5 V
$I_{RM}$	$I_F = I_T, V_{GE} = 0\text{ V}, -di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $I_F = 1\text{ A}; -di/dt = 100\text{ A}/\mu\text{s}; V_R = 30\text{ V}$		6	A
$t_{rr}$		$T_J = 100^\circ\text{C}$	100	ns
		$T_J = 25^\circ\text{C}$	25	ns
$R_{thJC}$				1.15 K/W

 Note: 1.  $I_T = 32\text{ A}$


**Fig. 1. Output Characteristics**

**Fig. 2. Extended Output Characteristics**

**Fig. 3. High Temperature Output Characteristics**

**Fig. 4. Temperature Dependence of  $V_{CE(sat)}$** 

**Fig. 5. Admittance Curves**

**Fig. 6. Capacitance Curves**

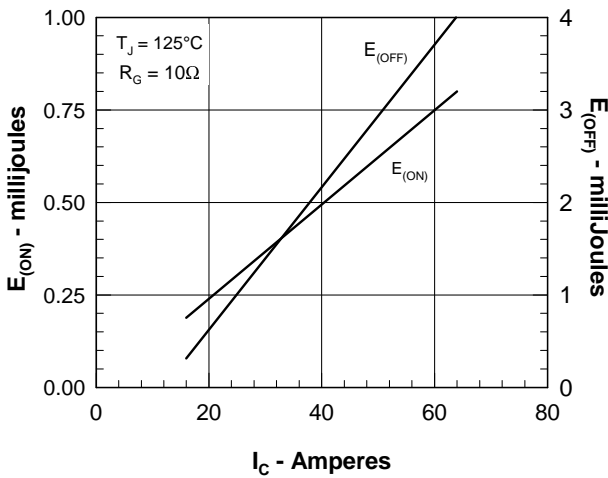


Fig. 7. Dependence of  $E_{ON}$  and  $E_{OFF}$  on  $I_C$ .

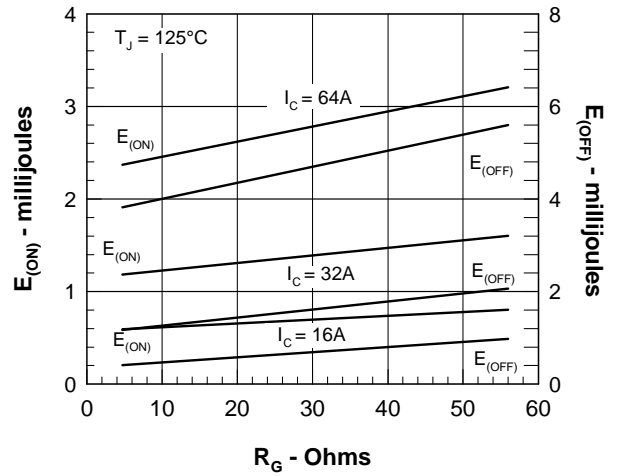


Fig. 8. Dependence of  $E_{ON}$  and  $E_{OFF}$  on  $R_G$ .

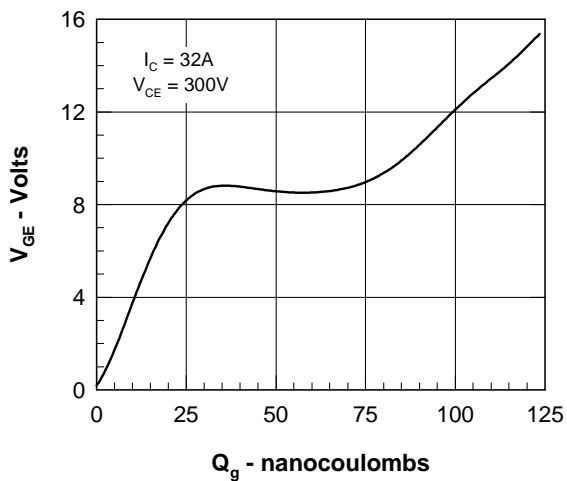


Fig. 9. Gate Charge

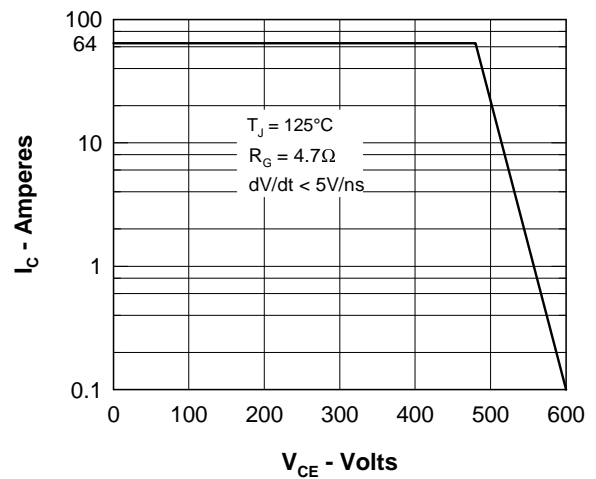


Fig. 10. Turn-off Safe Operating Area

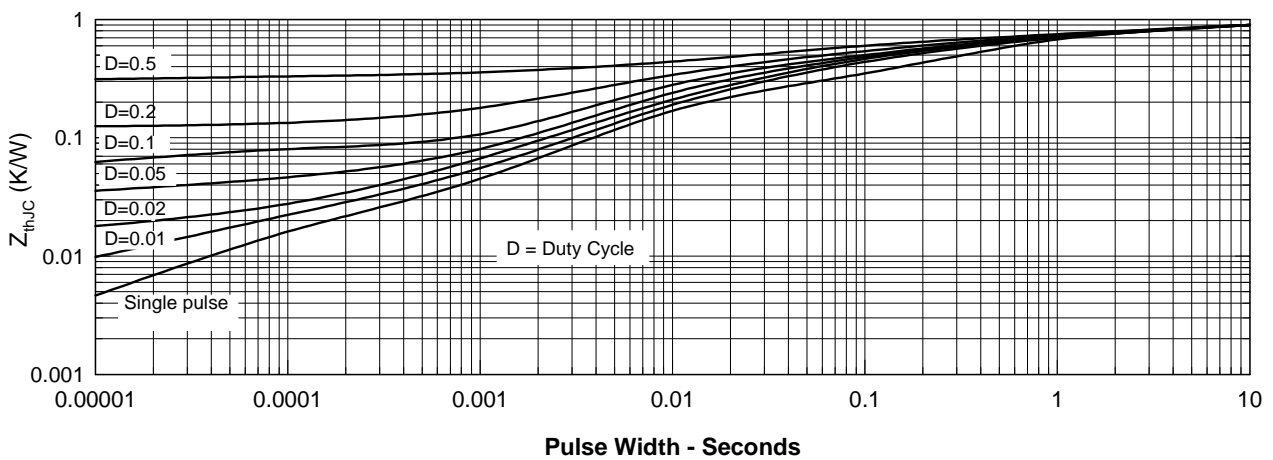


Fig. 11. Transient Thermal Resistance

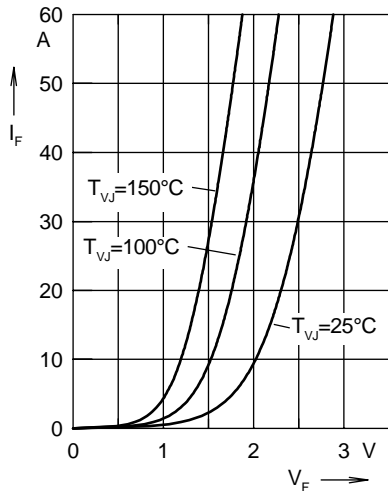


Fig. 12. Forward current  $I_F$  versus  $V_F$

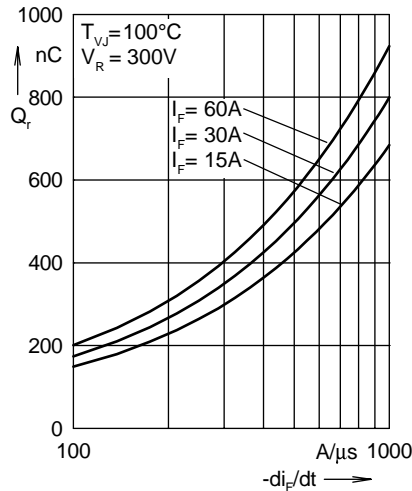


Fig. 13. Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

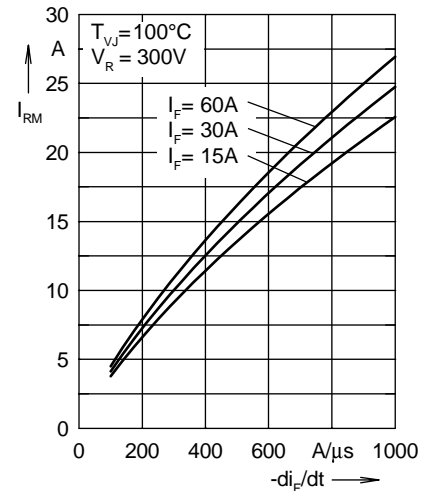


Fig. 14. Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

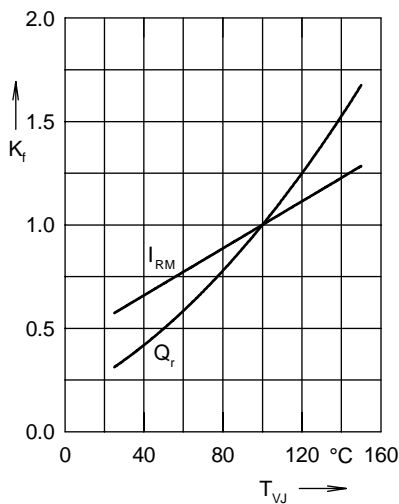


Fig. 15. Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

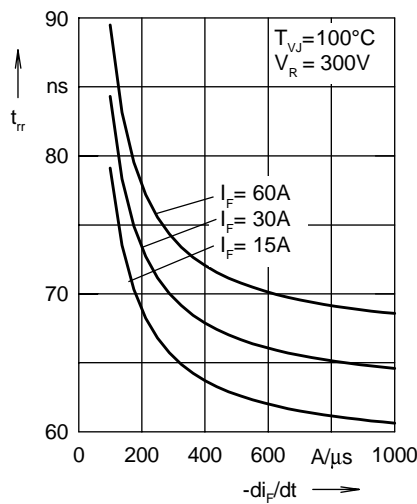


Fig. 16. Recovery time  $t_{rr}$  versus  $-di_F/dt$

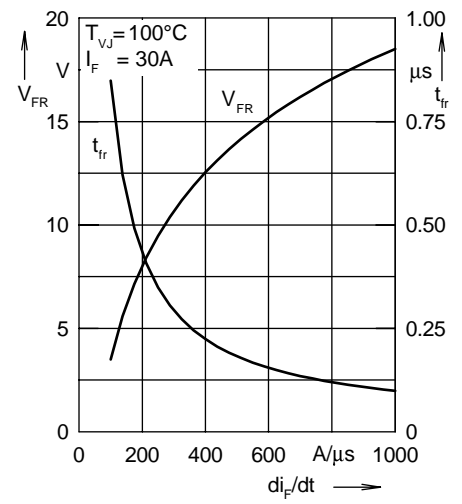


Fig. 17. Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

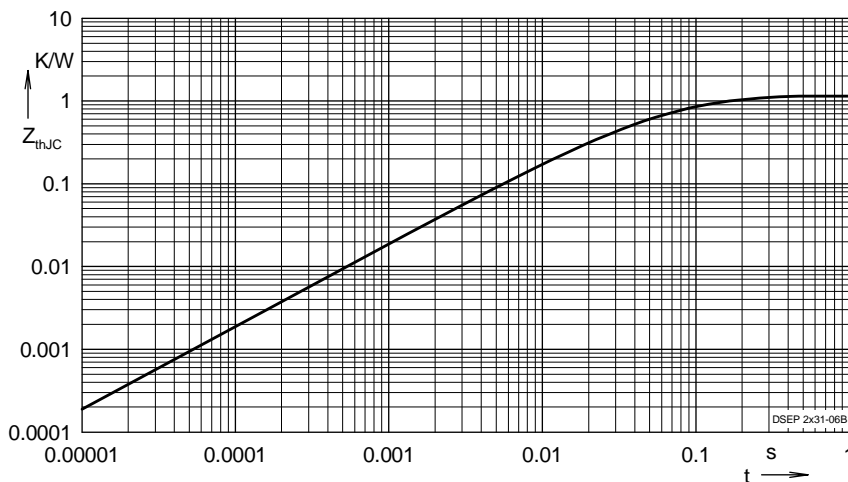


Fig. 18. Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.436	0.0055
2	0.482	0.0092
3	0.117	0.0007
4	0.115	0.0418